

**In the Specification:**

At page 1, the paragraph inserted before the "Technical Field" by the amendment dated January 14, 2002, has been replaced with the paragraph shown below:

**CROSS REFERENCE TO RELATED APPLICATION**

This patent application is a Divisional Application of U.S. Patent Application Serial No. 09/026,042, filed February 19, 1998, now U.S. Patent No. 6,395,128 B2, issued May 28, 2002, entitled "RF Powered Plasma Enhanced Chemical Vapor Deposition Reactor and Methods of Effecting Plasma Enhanced Chemical Vapor Deposition," naming Sujit Sharan, Gurtej S. Sandhu, Paul Smith and Mei Chang as inventors, the disclosure of which is incorporated by reference. This application is related to U.S. Patent No. 6,159,867, filed August 19, 1999, which is a divisional application of U.S. Patent No. 6,112,697, filed February 19, 1998.